

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

Docket Number	Application Number
M4065.0210/P210-A	Not Yet Assigned
Applicant(s)	
Dan Gealy et al.	
Filing Date	Group Art Unit
December 5, 2001	2814



12/05/01

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
WJ		5142438	08/14/92	Reinberg et al.	341	313	

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translations	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

WJ	A	G. W. Dietz et al., "LEAKAGE CURRENTS IN Ba _{0.7} Sr _{0.3} TiO ₃ THIN FILMS FOR ULTRAHIGH-DENSITY DYNAMIC RANDOM ACCESS MEMORIES," J. Appl. Phys. 82 (5), September 1, 1997, American Institute of Physics, pages 2359-2364.*
	B	Tomonori Aoyama et al., "ULTRATHIN Ta ₂ O ₅ FILM CAPACITOR WITH Ru BOTTOM ELECTRODE," J. Electrochem. Soc. Vol. 145, No. 8, August 1998, The Electrochemical Society, Inc., pages 2961-2963.*
	C	Benjamin Chih-ming Lai et al., "LEAKAGE CURRENT MECHANISM OF METAL-Ta ₂ O ₅ METAL CAPACITORS FOR MEMORY DEVICE APPLICATION," Journal of the Electrical Society, 146 (1) pages 266-269 (1999).*

EXAMINER	DATE CONSIDERED
Not Yet Assigned	WJ/Trish 12/23/02
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.	